

# OPA9445L

## Infrared LED Chip

GaAlAs /GaAs

**1.Material**  
Substrate GaAs (N Type)  
Epitaxial Layer GaAlAs (P/N Type)

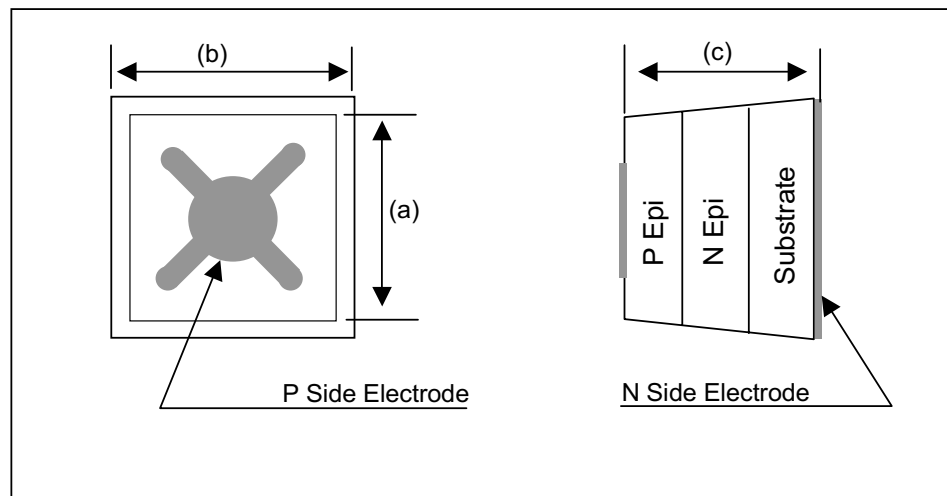
**2.Electrode**  
N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy

### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.2		V	$I_F=20\text{mA}$
	$V_{F(2)}$		1.4	1.6	V	$I_F=100\text{mA}$
Reverse Voltage	$V_R$	5.0	30		V	$I_R=10\mu\text{A}$
Power	$P_{O(1)}$		5		mW	$I_F=20\text{mA}$
	$P_{O(2)}$	16	22		mW	$I_F=100\text{mA}$
Wavelength	$\lambda_P$		940		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		45		nm	$I_F=20\text{mA}$

Note : Assembled into T1<sup>3</sup>/<sub>4</sub> plastic package.

**4. Mechanical Data**  
(a) Emission Area ----- 12mil × 12mil  
(b) Bottom Area ----- 14mil × 14mil  
(c) Chip Thickness ----- 11mil



Knowledge\*on Inc.

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